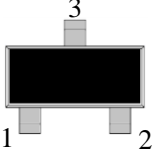


1、Features

- High dense cell design for extremely low RDS(ON)
- Exceptional on-resistance and maximum DC current capability
- Load/Power Switching
- Interfacing Switching

2、Pinning information

PIN	Description	Simplified outline
1	GATE(G)	
2	SOURCE(S)	
3	DRAIN(D)	

3、Limiting value

(Ta = 25°C unless otherwise noted).

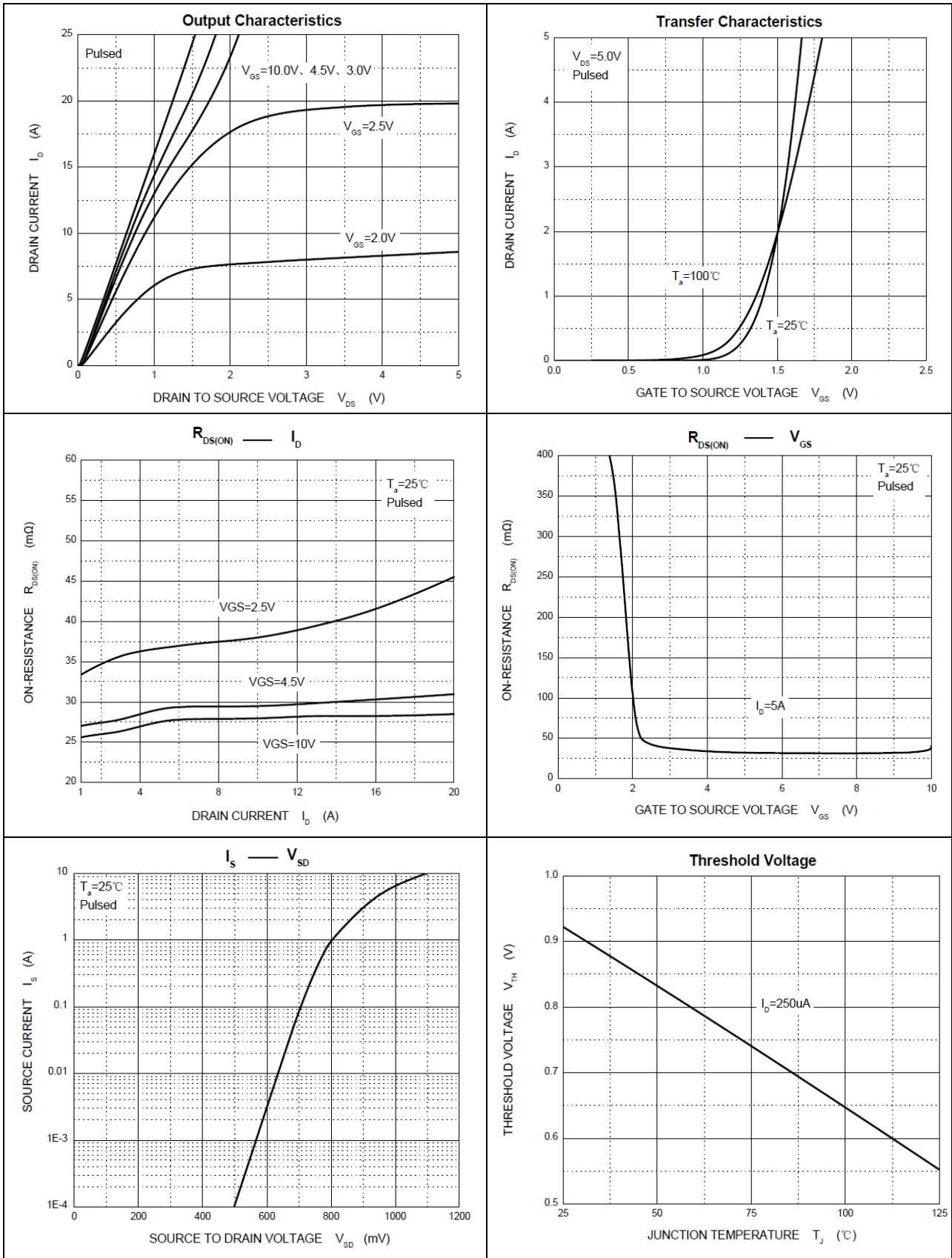
SYMBOL	PARAMETER	Limit	UNIT
Vds	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±12	V
Id	Continuous Drain Current	5.8	A
Pd	Power Dissipation	350	mW
RθJA	Thermal Resistance from Junction to Ambient	357	°C/W
Tj	Operating Junction Temperature	+150	°C
Tstg	Operating Junction and Storage Temperature Range	-50 to +150	°C

4、Electrical Characteristics (Ta = 25°C unless otherwise noted)

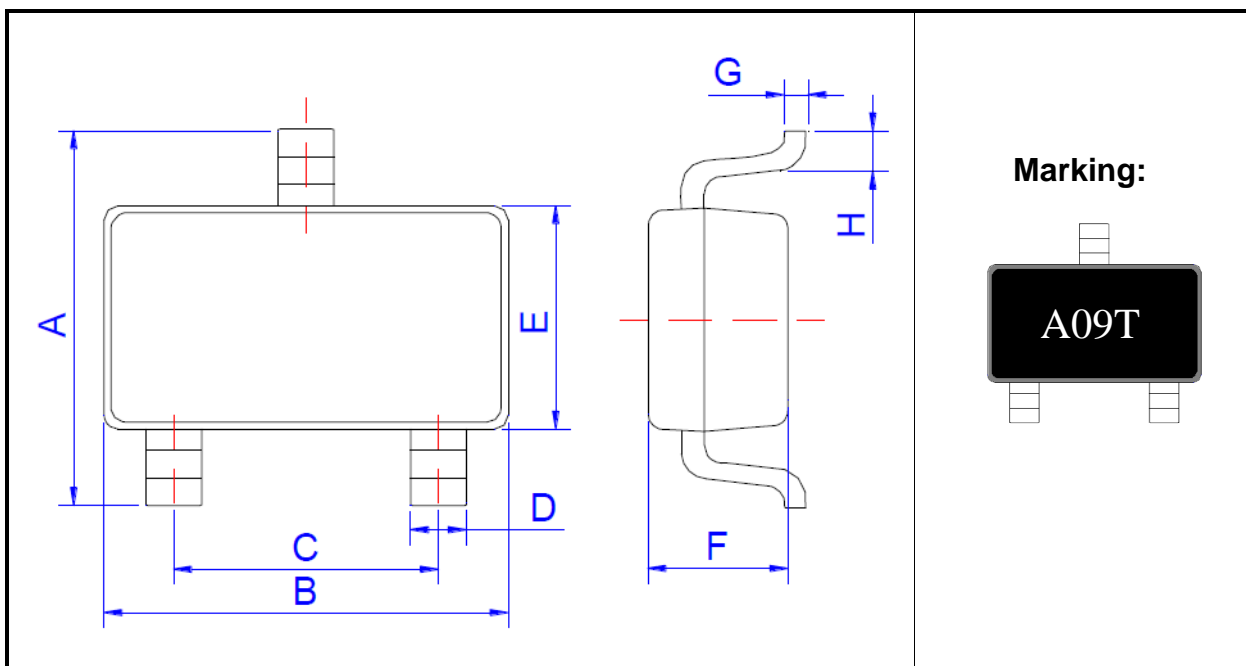
SYMBOL	PARAMETER	CONDITIONS	MIN	Typ	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	VGS=0 V, ID=250 μA	30			V
V _{th(GS)}	Gate-Threshold Voltage	VDS=VGS, ID=250 μA	0.7		1.4	V
I _{GSS}	Gate-body Leakage	VDS=0 V, VGS=±12V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	VDS=24 VGS=0 V			1	u
R _{DS(ON)}	Drain-Source On-Resistance	VGS=10 V, ID=5.8A			35	mΩ
		VGS=4.5 V, ID=5A			40	
		VGS=2.5 V, ID=4A			52	
g _{fs}	Forward Trans conductance	VDS=5V, ID=5A	8			S
V _{SD}	Diode Forward Voltage	IS=1A, VGS=0 V			1.0	V
C _{iss}	Input Capacitance*	VDS=15V, VGS=0V, f=1MHz			1050	pF
C _{oss}	Output Capacitance*			99		pF
C _{rss}	Reverse Transfer Capacitance*			77		pF
T _{d(on)}	Turn-on Time*	VDS=15V, VGS=10V RL=2.7 Ω, RG=3 Ω			5	nS
T _{d(off)}	Turn-off Time*				40	nS

*These parameters have no way to verify.

5. Electrical Characteristics Curve



6、Package outline(SOT-23)



DIM	Inches			Milimeters		
	Min	Type	Max	Min	Type	Max
A	0.104		0.116	2.65		2.95
B		0.115			2.92	
C		0.075			1.90	
D	0.014		0.018	0.35		0.45
E		0.051			1.30	
F		0.043			1.10	
G		0.006			0.16	
H	0.010		0.022	0.25		0.55